

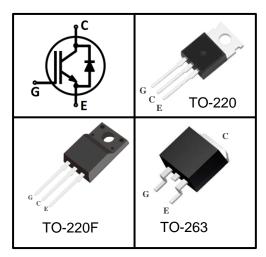
#### **Features**

- Easy parallel switching capability due to positive temperature coefficient in V<sub>CEsat</sub>
- Low  $V_{CEsat}$ , fast switching
- High ruggedness, good thermal stability
- Very tight parameter distribution

Туре	Marking	Package Code
MPBP15N65EF	MP15N65EF	TO-220-3
MPBA15N65EF	MP15N65EF	TO-220F-3
MPBC15N65EF	MP15N65EF	TO-263

## **Applications**

**Motor Drives** 



#### Maximum Rated Values 1

Parameter	Cymhol	Value			Unit
Farameter	Symbol	220	220F	263	
Collector-emitter voltage	V <sub>CE</sub>		650		V
DC collector current <sup>2</sup>					
T <sub>C</sub> =25°C			30		
T <sub>C</sub> =100°C	T <sub>C</sub>				
Pulsed collector current <sup>3</sup>	I <sub>Cpuls</sub>		45		A
Diode forward current <sup>2</sup>					
T <sub>C</sub> =25°C			30		
T <sub>C</sub> =100°C	-  I <sub>F</sub>	15			
Diode pulsed current <sup>3</sup>	I <sub>Fpuls</sub>	45			
Short circuit withstanding time V <sub>GE</sub> = 15V, V <sub>CC</sub> ≤ 400V, T <sub>J</sub> ≤150°C	t <sub>SC</sub>	5		us	
Gate-emitter voltage	±20			V	
Transient Gate-emitter voltage (t <sub>p</sub> ≤10us) V <sub>GE</sub>			±30		V
Power dissipation					
T <sub>C</sub> =25°C	D		52	107	W
T <sub>C</sub> =100°C	- P <sub>tot</sub>	63	26	54	
Operating junction temperature	T <sub>j</sub>	-55~175		°C	
Storage temperature	T <sub>stg</sub>	-55~150		)	

<sup>1:</sup>Reference standard: JESD-022 2: limited by Tjmax 3: Tp limited by Tjmax ;



### **Thermal Characteristics**

Parameter	Symbol		Unit		
Falameter	Symbol	220	220F	263	Offic
IGBT thermal resistance, junction-	R <sub>thJC</sub>	1.2	2.9	1.4	
case	' `thJC	1.2	2.	1.7	
Diode thermal resistance, junction-	R <sub>thJCD</sub>	2.0	4.6	2.8	K/W
case	tribCD				
Thermal Resistance, junction-ambient	R <sub>thJA</sub>	65	65	65	

# Electrical Characteristics (at Tj=25°C, unless otherwise specified) Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter breakdown voltage	V <sub>(BR)CES</sub>	V <sub>GE</sub> =0V, I <sub>C</sub> =0.25mA	650	-	-	
Collector-emitter		V <sub>GE</sub> =15V, I <sub>C</sub> =15A T <sub>j</sub> =25°C	1	1.30	1.80	
saturation voltage	V <sub>CE(sat)</sub>	T <sub>j</sub> =125°C	-	1.55	-	
		T <sub>j</sub> =150°C	-	1.65	-	V
Diada famuand valtaga	V <sub>F</sub>	V <sub>GE</sub> =0V,I <sub>F</sub> =15A T <sub>j</sub> =25℃	-	1.50	1.80	
Diode forward voltage		T <sub>j</sub> =125°C	-	1.40	-	
		T <sub>j</sub> =150°C	-	1.30	-	
G-E threshold voltage	$V_{GE(th)}$	$I_C=250uA, V_{CE}=V_{GE}$	4.5	5.8	6.5	
C-E leakage current	I <sub>CES</sub>	V <sub>CE</sub> =650V, V <sub>GE</sub> =0V T <sub>j</sub> =25°C	-	-	0.01	mA
		T <sub>j</sub> =150°C	-	-	1.0	
G-E leakage current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> =20V	-	-	250	nA



## **Dynamic Characteristics**

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input capacitance	C <sub>iss</sub>	\/ _25\/	-	2091	1	
Output capacitance	C <sub>oss</sub>	V <sub>CE</sub> =25V, V <sub>GE</sub> =0V,	1	69	1	рF
Reverse transfer capacitance	C <sub>rss</sub>	f=1MHz	-	32	-	•
Gate charge	$Q_G$	V <sub>CC</sub> =300V, I <sub>C</sub> =15A, V <sub>GE</sub> =15V	-	113	-	nC

## **IGBT Switching Characteristics**

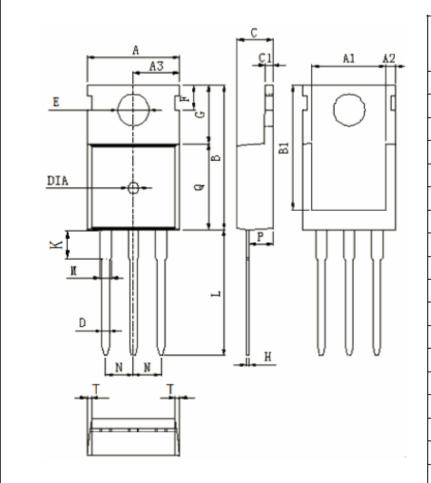
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Turn-on delay time	t <sub>d(on)</sub>		-	68	-	
Rise time	t <sub>r</sub>	] T <sub>i</sub> =25°C,	-	30	-	
Turn-off delay time	t <sub>d(off)</sub>	T <sub>j</sub> =25°C, V <sub>CC</sub> =400V,	-	174	-	ns
Fall time	t <sub>f</sub>	I <sub>C</sub> =15A, V <sub>GE</sub> =0/15V, R <sub>G</sub> =10Ω,	-	58	1	
Turn-on energy	E <sub>on</sub>	$R_{G}=10\Omega$ ,	-	0.26	1	
Turn-off energy	E <sub>off</sub>	Inductive load	-	0.31	-	mJ
Total switching energy	E <sub>ts</sub>		-	0.57	-	

#### **Diode Characteristics**

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Diode reverse recovery time	t <sub>rr</sub>	T <sub>i</sub> =25°C,	1	78	1	ns
Diode reverse recovery charge	Q <sub>rr</sub>	V <sub>R</sub> =400V, I <sub>F</sub> =15A,	1	0.458	1	μC
Diode peak reverse recovery current	I <sub>rrm</sub>	di <sub>F</sub> /dt=570A/µs	-	10.1	-	A



## TO-220-3L

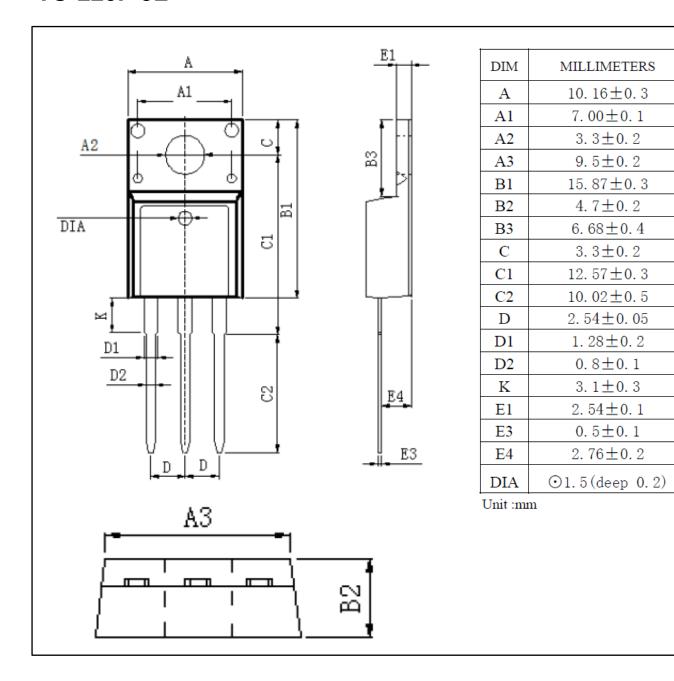


DIM	MILLIMETERS
A	10.0±0.3
A1	$8.64\pm0.2$
A2	1.15±0.1
A3	5.0±0.2
В	15.8±0.4
B1	13.2±0.3
C	$4.56\pm0.1$
C1	1.3±0.2
D	0.8±0.2
E	3.6±0.2
F	$2.95\pm0.3$
G	6.5±0.3
H	0.5±0.1
K	3.1±0.2
L	13. $2\pm0.4$
M	1.25±0.1
N	$2.54\pm0.1$
P	2. 4±0. 3
Q	9.0±0.3
T	₩:0.35
DIA	⊙1.5(deep 0.2)

Unit:mm

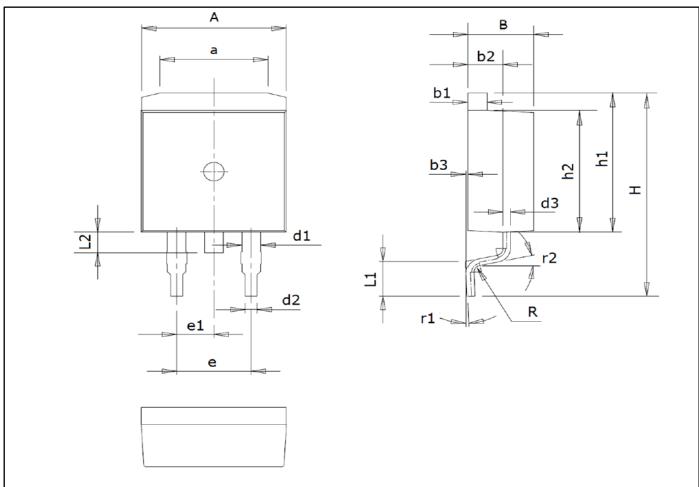


#### TO-220F-3L





## **TO-263**



Symbol	Dimensions (mm)	Symbol	Dimensions (mm)	Symbol	Dimensions (mm)
Α	9.86~10.26	d2	0.7~0.96	L1	2.0~2.6
а	7.0~7.8	d3	0.3~0.53	L2	1.3~1.8
В	4.37~4.77	е	5.08	R	0.5
b1	1.22~1.42	e1	2.54	r1	0-9°
b2	2.2~2.6	Н	14.7~15.5	r2	12°
b3	0~0.25	h1	10.3~10.7		
d1	1.17~1.47	h2	9.1~9.4		



## **Revision History:**

Revision	Date	Subjects (major changes since last revision)
1.0	2022-01	Initial version



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